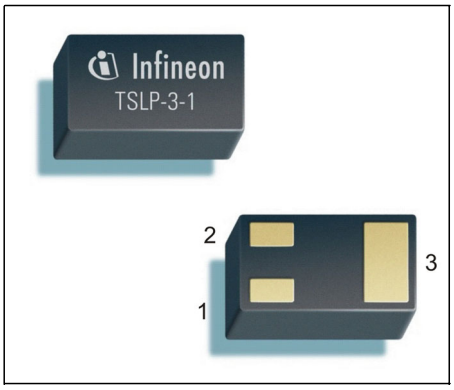
Low Noise Silicon Bipolar RF Transistor



- For low voltage / low current applications
- Ideal for VCO modules and low noise amplifiers
- Low noise figure: 1.1 dB at 1.8 GHz
- Excellent ESD performance
  typical value 1500V (HBM)
- High f_T of 22 GHz
- Pb-free (RoHS compliant) and halogen-free thin small leadless package
- Qualification report according to AEC-Q101 available

RoHS

ESD (**E**lectro**s**tatic **d**ischarge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR460L3	AB	1 = B	2 = E	3 = C	TSLP-3-1

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
T_A = 25 °C		4.5	
T_A = -55 °C		4.2	
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	50	mA
Base current	I_B	5	
Total power dissipation[1)] $T_S \leq 108$°C	P_{tot}	200	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{Stg}	-55 ... 150	

[1] T_S is measured on the collector lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	210	K/W

Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	4.5	5.8	-	V
Collector-emitter cutoff current V_{CE} = 15 V, V_{BE} = 0	I_{CES}	-	-	10	µA
Collector-base cutoff current V_{CB} = 5 V, I_E = 0	I_{CBO}	-	-	100	nA
Emitter-base cutoff current V_{EB} = 0,5 V, I_C = 0	I_{EBO}	-	-	1	µA
DC current gain I_C = 20 mA, V_{CE} = 3 V, pulse measured	h_{FE}	90	120	160	-

[1]For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

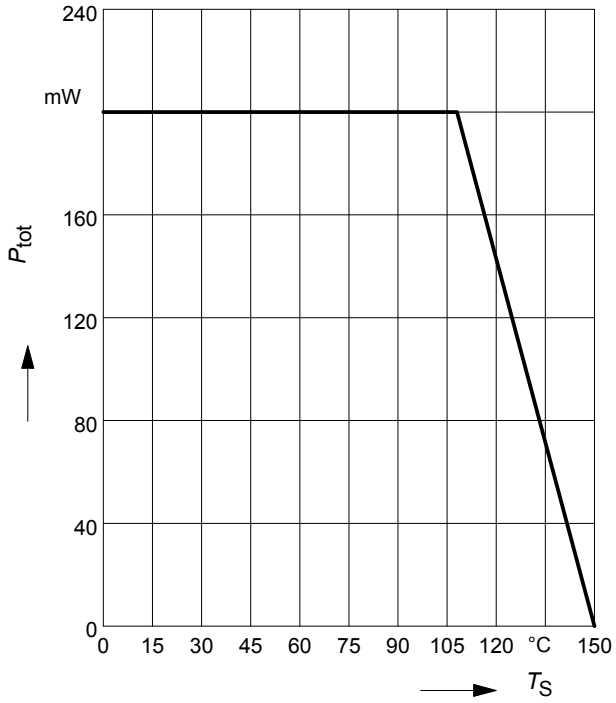
Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency I_C = 30 mA, V_{CE} = 3 V, f = 1 GHz	f_T	16	22	-	GHz
Collector-base capacitance V_{CB} = 3 V, f = 1 MHz, V_{BE} = 0 , emitter grounded	C_{cb}	-	0.28	0.45	pF
Collector emitter capacitance V_{CE} = 3 V, f = 1 MHz, V_{BE} = 0 , base grounded	C_{ce}	-	0.14	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz, V_{CB} = 0 , collector grounded	C_{eb}	-	0.55	-	
Minimum noise figure I_C = 5 mA, V_{CE} = 3 V, Z_S = Z_{Sopt} , f = 1.8 GHz f = 3 GHz	NF_{min}	 - -	 1.1 1.35	 - -	dB
Power gain, maximum stable[1)] I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 1.8 GHz	G_{ms}	-	16.0	-	dB
Power gain, maximum available[1)] I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt} , f = 3 GHz	G_{ma}	-	11	-	dB
Transducer gain I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_L = 50Ω, f = 1,8 GHz f = 3 GHz	$\lvert S_{21e}\rvert^2$	 - -	 14 10	 - -	dB
Third order intercept point at output[2)] V_{CE} = 3 V, I_C = 20 mA, f = 1.8 GHz	$IP3$	-	27	-	dBm
1dB compression point at output I_C = 20 mA, V_{CE} = 3 V, f = 1.8 GHz	P_{-1dB}	-	11.5	-	

[1] $G_{ma} = \lvert S_{21} / S_{12}\rvert (k-(k^2-1)^{1/2})$, $G_{ms} = \lvert S_{21} / S_{12}\rvert$

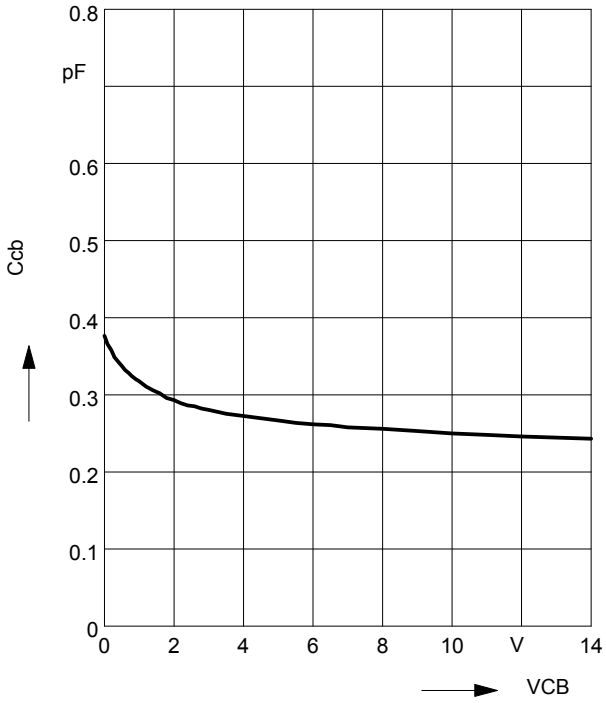
[2] IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

Total power dissipation $P_{tot} = f(T_S)$



Collector-base capacitance $C_{cb} = f(V_{CB})$

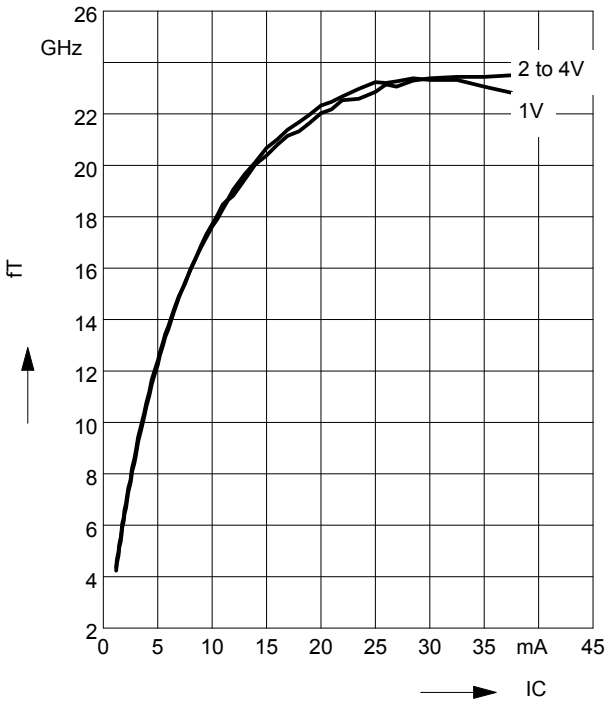
f = 1MHz



Transition frequency $f_T = f(I_C)$

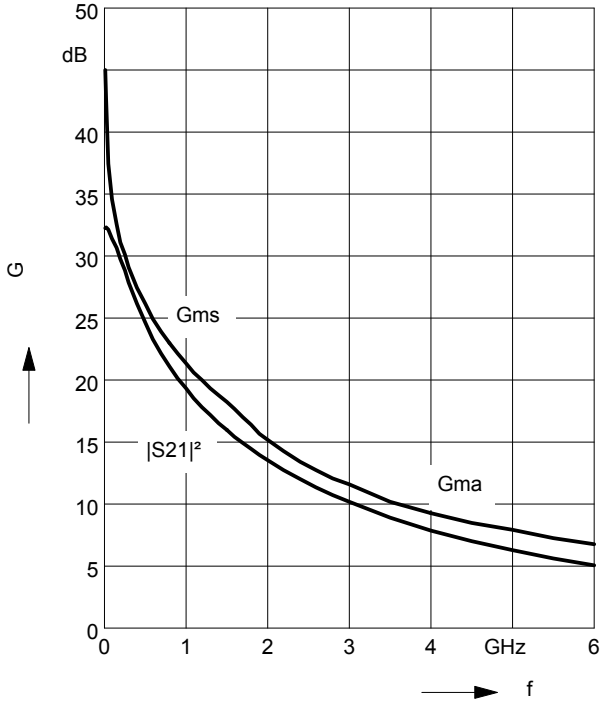
f = 1 GHz

V_{CE} = parameter in V



Power gain G_{ma}, G_{ms}, $|S_{21}|^2 = f(f)$

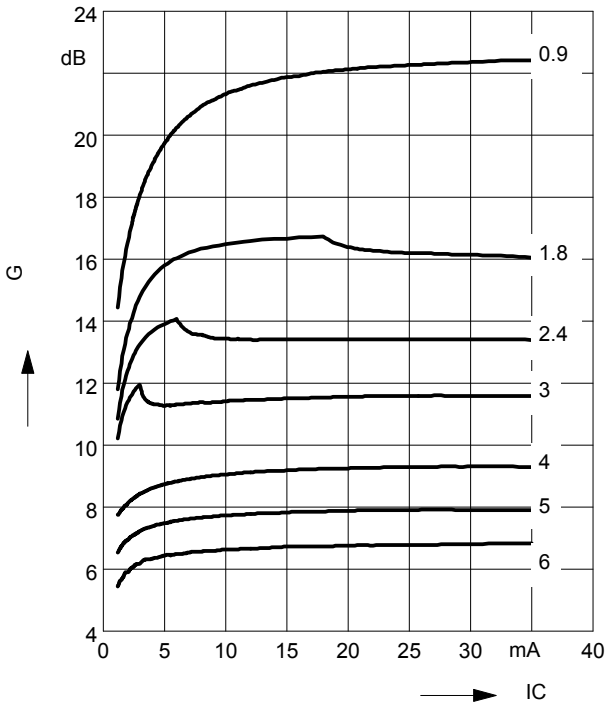
V_{CE} = 3 V, I_C = 20 mA



Power gain G_{ma}, G_{ms} = f (I_C)

V_{CE} = 3V

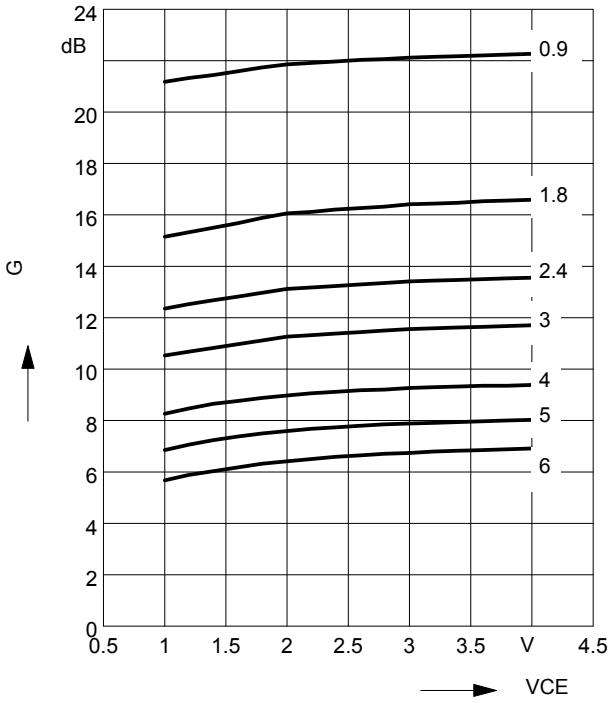
f = parameter in GHz



Power gain G_{ma}, G_{ms} = f (V_{CE})

I_C = 20 mA

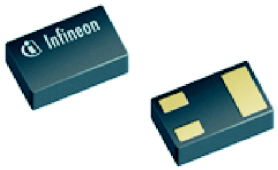
f = parameter in GHz

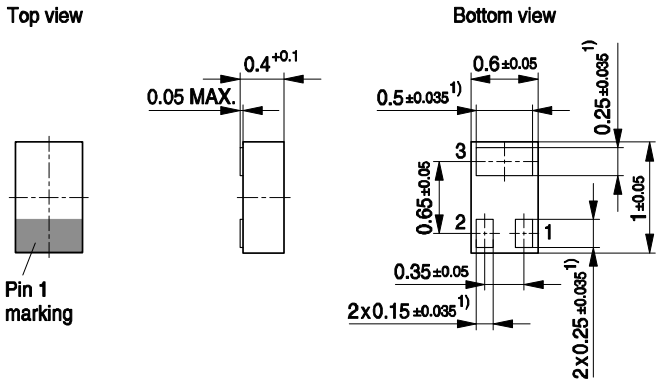


SPICE GP Model

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.
Please consult our website and download the latest versions before actually starting your design. You find the BFR460L3 SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device. The model parameters have been extracted and verified up to 6 GHz using typical devices. The BFR460L3 SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.

Package Outline

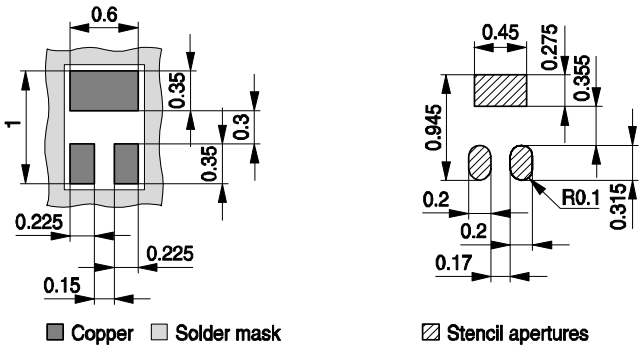




1) Dimension applies to plated terminal

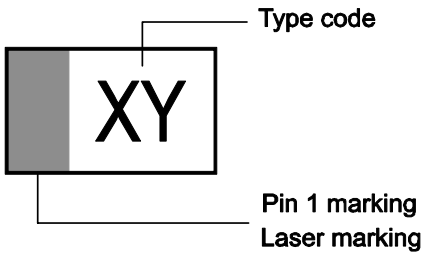
TSLP-3-1-PO V03

Foot Print



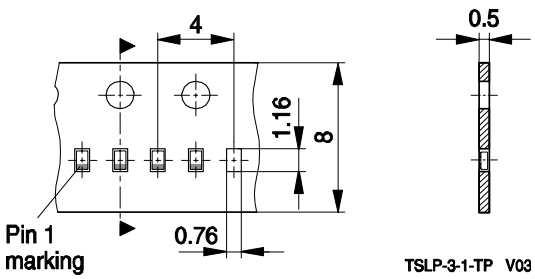
TSLP-3-1-FP V01

Marking Layout (Example)



Standard Packing

Reel Ø 330 mm: 15.000 Pieces/ Reel



TSLP-3-1-TP V03

Edition 2009-11-16

Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<www.infineon.com>).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.
Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.